

TITLE OF THE INVENTION
CRYSTALLIZATION APPARATUS AND CRYSTALLIZATION METHOD

CROSS-REFERENCE TO RELATED APPLICATIONS

This application is based upon and claims the
5 benefit of priority from the prior Japanese Patent
Application No. 2002-319267, filed November 1, 2002,
the entire contents of which are incorporated herein by
reference.

BACKGROUND OF THE INVENTION

10 1. Field of the Invention

The present invention relates to a crystallization
apparatus and a crystallization method of
semiconductor, and more particularly to an apparatus,
a method, a mask and others for generating
15 a crystallized semiconductor film by irradiating
a polycrystal semiconductor film or an amorphous
semiconductor film with a laser beam through a mask.

2. Description of the Related Art

Materials of a thin film transistor (TFT) used
20 for a switching element or the like which controls
a voltage to be applied to pixels of, e.g., a liquid
crystal display (LCD) are conventionally roughly
divided into amorphous silicon and polysilicon.

The polysilicon has higher electron mobility than
25 that of the amorphous silicon. Therefore, when
a transistor is formed by using the polycrystal
silicon, a switching speed is increased as compared

with a case using the amorphous silicon, and a response speed of a display is also increased. Further, such a transistor can be used as a thin film transistor of a peripheral LSI. Furthermore, using such a transistor
5 can obtain advantages such as a reduction in design margin of any other components.

In case of incorporating peripheral circuits such as a driver circuit or a DAC other than a display main body into a display, constituting these peripheral
10 circuits by the transistors enables an operation at a higher speed.

The polycrystal silicon consists of a number of crystal grains, and it has lower electron mobility than that of monocrystal silicon or crystallized silicon.

Moreover, in a small transistor formed by using the
15 polysilicon, irregularities in a crystal grain boundary number at a channel portion are a problem. Thus, in recent years, there has been proposed a crystallization method which generates monocrystal silicon with a large
20 particle diameter in order to improve the electron mobility and reduce irregularities in a crystal grain boundary number at the channel portion.

As this type of crystallization method, there is known "phase control ELA (Excimer Laser Annealing)"
25 which generates a crystallized semiconductor film by irradiating a phase shift mask neighboring a polycrystal semiconductor film or an amorphous

semiconductor film in parallel with an excimer laser beam. The detail of the phase control ELA is disclosed in, e.g., "Surface Science Vol. 21, No. 5, pp. 278-287, 2000".

5 In the phase control ELA, the phase shift mask generates a light intensity distribution having an inverse peak pattern. In this pattern, a light intensity is minimum or substantially 0 at a point corresponding to a phase shift portion of the phase shift mask (pattern that a light intensity is
10 substantially 0 at the center and it is suddenly increased toward the periphery) is generated. A polycrystal semiconductor film or an amorphous semiconductor film is irradiated with the light having
15 this light intensity distribution with the inverse peak pattern. As a result, a temperature gradient is generated in a fusion area of the semiconductor film in accordance with the light intensity distribution, and a crystal nucleus is formed at a part which is first
20 solidified in accordance with the point where the light intensity is minimum or substantially 0. Then, a crystal grows in a lateral direction (lateral growth) from the crystal nucleus toward the periphery, thereby generating monocrystal grains with a large particle
25 size.

 In a prior art, a generally used phase shift mask is a so-called line type phase shift mask constituted

by two types of rectangular areas which are alternately repeated along one direction. A phase difference of π (180 degrees) is given between the two different-type areas. In this case, as shown in FIG. 22, a boundary 200 between two different-type areas 201 and 202 having different thicknesses or different phases constitutes a phase shift portion. The polycrystal semiconductor film or the amorphous semiconductor film is irradiated with the light which has been transmitted through such a phase shift mask. The irradiated light has a light intensity distribution with an inverse peak pattern portion RP such that a light intensity is substantially 0 or minimum at a position on a line corresponding to the phase shift portion 200 and the light intensity is one-dimensionally increased toward the periphery.

As described above, in the prior art using the line type phase shift mask, a temperature becomes lowest along a line corresponding to the phase shift portion (boundary 200), and a temperature gradient is generated along a direction orthogonal to a line corresponding to the phase shift portion. Further, it is general that the light intensity distribution (curved line) at a middle portion MP between the two adjacent inverse peak pattern portions RP involves irregular undulations (wave-formed distribution such as that an increase and a decrease in the light intensity are repeated).

In this case, it is desirable for the positional control of a crystal nucleus that the crystal nucleus is generated at a position with a large inclination or a position 210 close to a minimum intensity point in the light intensity distribution with the inverse peak pattern portion RP. However the crystal nucleus may be inconveniently generated at a position 220 with the low light intensity (i.e., an undesired position) in the undulations of the middle portion. Furthermore, even if the crystal nucleus is generated at an undesirable position, the lateral growth which has started from the crystal nucleus toward the periphery tends to stop at a part where the light intensity is decreased near the boundary between the inverse peak pattern portion RP and the middle portion MP.

BRIEF SUMMARY OF THE INVENTION

It is an object of the present invention to provide a crystallization apparatus and a crystallization method which can generate a crystal nucleus or nuclei at only a desired position or portions, and realize a sufficient lateral growth from the crystal nucleus, thereby generating a crystallized semiconductor film with a large particle size.

To achieve this aim, according to a first aspect of the present invention, there is provided a crystallization apparatus comprising an illumination system which illuminates a mask and generates

a crystallized semiconductor film by irradiating
a polycrystal semiconductor film or an amorphous
semiconductor film with a light ray having a light
intensity distribution with an inverse peak pattern
5 through the mask. The mask includes a light absorption
layer having light absorption characteristics according
to the light intensity distribution with the inverse
peak pattern, a light scattering layer having light
scattering characteristics, a light reflection layer
10 having light reflection characteristics, a light
refraction layer having light refraction
characteristics, and/or a light diffraction layer
having light diffraction characteristics.

One of the first layer and the second layer can be
15 substituted by a phase shift layer.

According to a second aspect of the present
invention, there is provided a crystallization method
which illuminates a mask, and generates a crystallized
semiconductor film by irradiating a polycrystal
20 semiconductor film or an amorphous semiconductor film
with a light ray having a light intensity distribution
with an inverse peak pattern through the mask. The
mask includes a light absorption layer having light
absorption characteristics according to the light
25 intensity distribution with the inverse peak pattern,
a light scattering layer having light scattering
characteristics, a light reflection layer having light

reflection characteristics, a light refraction layer having light refraction characteristics, and/or a light diffraction layer having light diffraction characteristics.

5 As described above, in the technique of the aspects according to the present invention, a conformation of a light intensity distribution with an inverse peak pattern obtained on a processed substrate can be entirely controlled by using a mask
10 which can arbitrarily form an intermediate light intensity distribution. Thus, a crystal nucleus can be generated at a desired position, and a sufficient lateral growth from the crystal nucleus can be realized, thereby generating a crystallized
15 semiconductor film with a large particle size.

 Objects and advantages of the invention will be set forth in the description which follows, and in part will be obvious from the description, or may be learned by practice of the invention. The objects and
20 advantages of the invention may be realized and obtained by means of the instrumentalities and combinations particularly pointed out hereinafter.

BRIEF DESCRIPTION OF THE SEVERAL VIEWS OF THE DRAWING

 The accompanying drawings, which are incorporated
25 in and constitute a part of the specification, illustrate embodiments of the invention, and together with the general description given above and the

detailed description of the embodiments given below,
serve to explain the principles of the invention.

FIG. 1 is a view schematically showing a structure
of a crystallization apparatus according to a first
5 embodiment of the present invention;

FIG. 2 is a view schematically showing a structure
and an effect of a basic unit part of a mask in the
first embodiment;

FIG. 3 is a view schematically showing a structure
10 of a basic unit part of a mask according to a first
modification and a light intensity distribution of
an outgoing light beam from this mask;

FIG. 4 is a view illustrating an effect of light
scattering layer of the mask depicted in FIG. 3;

15 FIG. 5 is a view basically illustrating scattering
of the light;

FIGS. 6A to 6E are views illustrating an example
of a manufacturing method of the mask according to the
first modification and a usage embodiment;

20 FIG. 7 is a view schematically showing a structure
of a basic unit part of a mask according to a second
modification and a light intensity distribution of
an outgoing light beam from this mask;

FIGS. 8A to 8E are views illustrating
25 a manufacture embodiment of the mask according to
the second modification and a usage embodiment;

FIG. 9 is a view showing a structure of a basic

unit part of a mask according to a third modification and a light intensity distribution of an outgoing light beam from this mask;

FIG. 10 is a view showing a simulation result
5 concerning a light intensity distribution obtained when a refraction surface of the mask according to the third modification is formed into a step-like shape;

FIG. 11 is a view schematically showing
10 a structure of a basic unit part of a mask according to a fourth modification and a light intensity distribution of an outgoing light beam from this mask;

FIG. 12 is a view illustrating a basic diffraction effect of the mask according to the fourth modification;

15 FIG. 13 is a view illustrating an example of a manufacturing method of the mask according to the fourth modification and a usage embodiment;

FIG. 14 is a view schematically showing
20 a structure of a crystallization apparatus according to a second embodiment of the present invention;

FIG. 15 is a view schematically showing
a structure of a crystallization apparatus according to a third embodiment of the present invention;

25 FIG. 16 is a view schematically showing a structure of a crystallization apparatus according to a fourth embodiment of the present invention;

FIG. 17 is a view schematically showing a primary

structure and an effect of a crystallization apparatus according to a fifth embodiment of the present invention;

FIG. 17A is a view showing a modification of the mask depicted in FIG. 17;

FIGS. 18A to 18C are views illustrating an example of a manufacturing method of a mask integrally constituted by a light reflection layer and a light absorption layer and a usage embodiment;

FIGS. 19A to 19D are views schematically showing a mask of a crystallization apparatus according to a sixth embodiment of the present invention and a light intensity distribution of an outgoing light beam from this mask, and FIG. 19E is a plan view showing a modification of the mask;

FIG. 20 is a view illustrating an example of a manufacturing method of a mask having binary distribution characteristics and a usage embodiment;

FIGS. 21A to 21E are views showing steps of an example of a method for manufacturing an electronic device by using the crystallization apparatus according to each embodiment; and

FIG. 22 is a view showing a light intensity distribution obtained on a processed substrate when a conventional line type phase shift mask is used.

DETAILED DESCRIPTION OF THE INVENTION

Embodiments according to the present invention

will now be described with reference to the accompanying drawings.

FIG. 1 is a view schematically showing a structure of a crystallization apparatus according to a first embodiment of the present invention. The crystallization apparatus according to the first embodiment includes an illumination system 2 which illuminates a mask 1. The illumination system 2 includes a KrF excimer laser light source 2a which supplies a laser beam having a wavelength of, e.g., 248 nm. As the light source 2a, it is also possible to use any other appropriate light source such as an XeCl excimer laser light source. The laser beam emitted from the light source 2a is expanded through a beam expander 2b, and then enters a first fly-eye lens 2c.

In this manner, a plurality of small light sources are formed on a rear focal plane of the first fly-eye lens 2c, and light fluxes from the small light sources illuminate an incident plane of a second fly-eye lens 2e through a first condenser optical system 2d in the superimposing manner. As a result, more small light sources than those on the rear focal plane of the first fly-eye lens 2c are formed on a rear focal plane of the second fly-eye lens 2e. Light fluxes from the small light sources formed on the rear focal plane of the second fly-eye lens 2e illuminate a mask 1 through a second condenser optical system 2f in

the superimposing manner.

Here, the first fly-eye lens 2c and the first
condenser optical system 2d constitute a first
homogenizer. An intensity concerning an incident angle
5 of the light onto the mask 1 is homogenized by the
first homogenizer. Further, the second fly-eye lens 2e
and the second condenser optical system 2f constitute
a second homogenizer. An intensity concerning an
in-plane position onto the mask 1 is homogenized by
10 the second homogenizer. Therefore, the illumination
system 2 irradiates the mask 1 with the light or laser
beam having a substantially even light intensity
distribution.

A substrate 3 processed to be arranged in parallel
15 to and in close proximity to the mask 1 is irradiated
with the laser beam which has passed through the
mask 1. Here, the processed substrate 3 is obtained by
sequentially forming an underlying film and an
amorphous silicon film on, e.g., a liquid crystal
20 display flat glass by a chemical vapor deposition
method. In other words, the mask 1 is set so as to
face the amorphous semiconductor film. The processed
substrate 3 is held at a predetermined position on
a substrate supporting stage 4 by a vacuum chuck or
25 an electrostatic chuck.

A structure and effect of a basic unit part of the
mask in the first embodiment will now be described with

reference to FIG. 2. The mask 1 is constituted by
a parallel plane type transparent substrate 1b made of
a transparent material such as a quartz glass, and
a light absorption layer 1c which is made of
5 a predetermined light absorption material and has
a predetermined surface shape. The mask has at least
one, or generally a plurality of basic unit parts 1a
arranged on the same plane, and only one basic unit
part 1a is shown in FIG. 2 for clarifying the drawing.
10 It is preferable for the mask 1 to have a conformation
that the basic unit parts 1a are actually
one-dimensionally repeated along a direction that
a transmittance distribution intensity varies
(horizontal direction in FIG. 2). That is, a plurality
15 of elongated rectangular areas are aligned in such
a manner that long sides of adjacent areas become
common in the horizontal direction of one substrate,
and a basic unit part 1a is formed in each rectangular
area. This point is also true in masks according to
20 the following modifications and embodiments.

As the light absorption material, it is possible
to adopt a material which is used in, e.g., a halftone
type phase shift mask, i.e., at least one of MoSi,
MoSiON, ZrSiO, a-Carbon, SiN/TiN, TiSiN, Cr and others.
25 In order to manufacture the mask 1, a light absorption
film consisting of, e.g., ZrSiO is formed with an even
thickness on the transparent substrate 1b, and then

a resist is applied on a surface of the light absorption film. Then, an electron beam lithography and development processing are applied by continuously changing a dose amount, and a resist film having
5 a continuous curved shape is formed in such a manner that both sides are thin and a center is thick in each basic unit part 1a. Thereafter, the resist film and a surface of the substrate under this film are removed from the resist film side to desired depths, by using
10 a dry etching technique. By such etching, a central part of the light absorption film having the thick resist film thereon is etched so as to be shallower than the both side parts having the thin resist film thereon. As a result, it is possible to obtain the
15 mask 1 including the light absorption layer 1c having a surface with a generally continuous curved shape step-shaped surface such as shown in FIG. 2.

The mask 1 including the light absorption layer 1c having a step-shaped surface (e.g., a surface
20 approximated by, e.g., eight-level steps) may be manufactured by, e.g., repeating formation and patterning of the light absorption film for a plurality of number of times. This technique will be described in detail hereinafter. First, a resist film is applied
25 except both outer side portions with a predetermined width of the light absorption film on each rectangular area of the substrate, and only the both outermost

portions are etched with a predetermined width and a predetermined depth by etching after removing the resist film. Then, new resist film is applied to the part of the light absorption film excluding the both
5 etched outermost portions and the outer portions with a predetermined width which are adjacent to the both outermost portions. Subsequently, the outer portion is etched with a predetermined width and a predetermined depth by the similar etching, and the outermost portion
10 is further etched with a depth corresponding to this etching depth. As a result, a step is formed between the outermost portion and the outer portion. In this manner, it is possible to form the light absorption film by performing this process for six times in such
15 a manner that the etching portions gradually shift toward the central portion so as to obtain a convex shape that the center most highly protrudes on eight level steps. This is just an example, and it can be understood that such steps may not be formed and the
20 number of steps is not restricted to eight.

When the mask 1 having such a structure is illuminated with the light or laser beam having a substantially even light intensity distribution by the illumination system 2, the light which has been
25 transmitted through the mask 1 has a light intensity distribution such that a light intensity is minimum at a position corresponding to the center of the convex

portion of the light absorption layer 1c on the surface
3a of the processed substrate and the light intensity
is monotonously increased toward the periphery, i.e.,
a light intensity distribution with an inverse peak
5 pattern (or a concave pattern).

As described above, the first embodiment uses the
mask 1 including the light absorption layer 1c having
light absorption characteristics according to a desired
light intensity distribution with an inverse peak
10 pattern. Thus, a conformation of the light intensity
distribution obtained on the processed substrate 3 can
be entirely controlled, and it is possible to obtain
a light intensity distribution that a light intensity
is monotonously increased from the center toward the
15 periphery as indicated by a curved line in FIG. 2.

The processed substrate irradiated the light having
such a light intensity distribution is heated according
the light intensity distribution. The temperature of
the heated portion of the substrate becomes higher than
20 a melting temperature of the substrate to growth
a crystal nucleus. The minimum light intensity of
the light may be set to heat an irradiated portion of
the substrate at a temperature lower or higher than
the melting temperature, or equal thereto. The light
25 having such a light intensity distribution is
irradiation in a pulse manner while shifting the
substrate. As a result, a crystal nucleus or nuclei

can be generated at a position where an inclination is large at a substantial center in the light intensity distribution with the inverse peak pattern (i.e., a desired position), and there is no part where
5 the light intensity is decreased in a middle part MP between adjacent inverse peak patterns RP, as different from the prior art. Thus, a growth of a large crystal is realized without preventing a lateral growth from stopping in mid course. In such a case, a maximum
10 protrusion portion of the light absorption film 1c, which is a central portion of each basic unit part 1a in this embodiment in such a mask 1a is accurately positioned on the transparent substrate 1b, and hence a crystal nucleus (nuclei) can be generated at
15 a desired position (portions) of the processed substrate 3a by accurately positioning the mask 1a and the processed substrate 3. Further, a sufficient lateral growth from the crystal nucleus can be realized, thereby generating a crystallized
20 semiconductor film with a large particle size.

A mask according to a first modification will now be described with reference to FIGS. 3 and 4. In the following explanation, since a material and a shape of the transparent substrate and a relationship between
25 the basic unit part and the mask are the same as those in the first embodiment unless otherwise stated, the detailed description will be eliminated. Referring to

FIG. 3, a basic unit part 11a of a mask 11 according to the first modification is constituted by a transparent substrate 11b and a light scattering layer 11c, the layer 11c is attached to one surface of the transparent substrate 11b and has light scattering characteristics according to a desired light intensity distribution with an inverse peak pattern. The light scattering layer 11c can be constituted by, e.g., forming fine roughness (surface relief) of a wavelength order of an illumination light ray on a light incident plane and/or a light outgoing radiation plane of a transparent layer, or forming a predetermined fine refractive index distribution in the transparent layer along the transparent layer.

When the light enters the light scattering layer 11c, there are generated light rays (direct transmission light) L1 which are directly transmitted without being scattered, light rays (backward scattered light) L2 which are scattered backwards, and light rays (forward scattered light) L3 which are scattered forwards as shown in FIG. 4. Although FIG. 4 illustrates that the backward scattered light L2 outgoes from the light incident plane and the forward scattered light L3 outgoes from the light outgoing radiation plane, positions from which the scattered light is emitted are not restricted thereto. It can be readily understood that such positions depend on

a structure of the scattering layer. When using such a mask, there is a possibility that the forward scattered light L3 reaches a surface 3a of the processed substrate and becomes a noise. In such
5 a case, however, by assuring a fixed gap between the mask 11 and the processed substrate 3, an intensity distribution of the forward scattered light which reaches the surface 3a becomes substantially even, and hence this light does not become a noise.

10 In this manner, basically, the light intensity distribution of the direction transmission light of the mask according to the first modification corresponds to the light intensity distribution formed on the surface 3a of the processed substrate 3.

15 Referring to FIG. 5, a basic description will be given as to scattering of the light. Generally, scattering due to particles b (for example, air gaps as described later) having a diameter a which is approximately a wavelength of the incident light can be
20 calculated by a Mie scattering theory. Referring to FIG. 5, an intensity I after a parallel beam with an intensity I_0 has passed through a substance with a thickness L , having particles b therein can be represented by the following expression (1). In the
25 expression (1), σ is a light intensity attenuation coefficient, and can be represented by the following expression (2).

$$I = I_0 e^{-\sigma L} \quad (1)$$

$$\sigma = NK\pi a^2 \quad (2)$$

Here, N is the number of particles per unit cubic volume, and a is a radius of the particle b .

5 Furthermore, K is a scattering efficiency of the particle, and is a value which can be calculated by the Mie scattering theory. When the radius a of the particle is not less than a wavelength, a value of K is approximately 4 to 2. As an example, assuming that the
10 radius a of the particle b is $0.39 \mu\text{m}$, the particle number N per unit cubic volume is $0.24/\mu\text{m}^3$ and the scattering efficiency K of the particle b is 2.0 (approximation), the attenuation coefficient σ is $0.23/\mu\text{m}$. Therefore, the light intensity I after
15 transmitted through a film with a thickness $L = 10 \mu\text{m}$ in which the particles are distributed with a density of N is $I = I_0 e^{-\sigma L} = 0.1 \times I_0$, and becomes a light intensity which is 1/10 of the intensity I_0 of the incident light.

20 In this manner, the distribution of the light intensity can be controlled by appropriately selecting the attenuation coefficient σ according to the expression (1) so as to differ depending on each position, or by changing thickness L of parts of a
25 material (basic layer) and appropriately distributing them. Although the attenuation coefficient σ can be increased as the radius a of the particle becomes

large, the forward scattered light is increased as compared with the backward scattered light and a scattered light component (= noise) which reaches the substrate 3 is also increased. Therefore, the design must be carried out taking this point into consideration.

An example of a manufacturing method of the mask according to the first modification and a usage embodiment will now be described with reference to FIGS. 6A to 6E.

Each of the particles b described above may be formed by any material and/or in any shape each as spherical, rectangular or irregular shape.

A resin layer 13 having a roughness surface or ridges and recesses was formed on the quartz glass substrate 11b as a base material as shown in FIG. 6B by resin molding using a die 12 depicted in FIG. 6A. The die 12 is an original plate formed by applying mechanical cutting processing to an Ni plate. Here, it was determined that a pitch P of ridges is 10 μm and a depth D of the recess is 5 μm . An organic SOG film (spin-on glass, e.g., a material obtained by, e.g., substituting alkoxysilane by alkyl) 14 having a flat upper face was formed on the resin 13 with the irregular shape by spin coating as shown in FIG. 6C after adding xylene 15 as a volatile matter which does not have a compatibility with this material.

Subsequently, by volatilizing the volatile matter 15 by drying, fine air gaps 16 having an average radius of approximately $0.4\ \mu\text{m}$ were generated in the organic SOG film as shown in FIG. 6D. At this time, since the surface of the SOG film 14 is flat, a film thickness distribution of the SOG film 14 depends on a layer thickness distribution of the resin mold layer 13, and a thickest part of the SOG film 14 was set to be approximately $10\ \mu\text{m}$ in this example. A refractive index of the SOG film 14 is approximately 1.5, and a refractive index of the air gap (air) 16 is 1. A difference in refractive index provokes scattering. The thus manufactured mask 11 was held at a position away from the processed substrate 3 by $20\ \mu\text{m}$, and the mask 11 was illuminated with an XeCl excimer laser beam (wavelength: 308 nm) from a substantially vertical direction. As a result, a desired light intensity distribution with an inverse peak pattern (concave pattern) was able to be formed, the a crystal with a large particle size can be generated. At this time, although the forward scattered light was generated, it became substantially even on the surface of the processed substrate, and its influence was able to be ignored.

A basic unit part of a mask according to a second modification will now be described with reference to FIG. 7. A basic unit part 21a of a mask 21 is

constituted by a transparent substrate 21b, and a light reflection layer 21c which is formed on a light outgoing radiation plane of the substrate 21b and has light reflection characteristics according to a desired light intensity distribution with an inverse peak pattern. The light reflection layer 21c is constituted as a multilayer reflection film formed according to a desired layer number distribution.

Since the multilayer reflection film has a structure in which dielectric substances with different refractive indices are alternately laminated and basically does not absorb the light, a value obtained by subtracting 1 from the refractive index is a transmittance. Therefore, a reflection factor is large (transmittance is small) in a part where the number of layers is large, and the reflection factor is small (transmittance is large) in a part where the number of layers is small. However, it is desirable to obtain a relationship between the number of layers in the multilayer reflection film and a value of the reflection factor by a rigid calculation in accordance with a desired light intensity pattern.

The light reflection layer 21c can be constituted as a metal reflection film formed in accordance with a predetermined thickness distribution. In this case, however, a thickness distribution must be controlled in an extremely thin metal reflection film.

An example of a manufacturing method of the mask according to the second modification and a usage embodiment will now be described with reference to FIGS. 8A to 8E. As shown in FIG. 8A, a multilayer reflection film 21c consisting of MgF_2 layers and ZnS layers was formed by alternately evaporating MgF_2 and ZnS on the quartz glass substrate 21b as a base material of the mask. Then, as shown in FIG. 8B, an electron beam resist 22 was spin-coated on the multilayer reflection film 21c. Thereafter, as shown in FIG. 8C, by performing irradiation and development while continuously changing a dose amount (irradiation quantity) by using an electron beam lithography device, a resist film 22 with an irregular or roughness corresponding to the desired light intensity distribution shape was obtained. Subsequently, a multilayer reflection film 21c having a predetermined layer number distribution and corresponding to the shape of the resist film 22 as shown in FIG. 8C was obtained as shown in FIG. 8D by performing dry etching to the resist film 22 and the multilayer reflection film 21c. Here, a part with a large layer number, i.e., a central portion has a high reflection factor, i.e., a low transmittance. On the contrary, parts with a small layer number, i.e., both side portions have a low reflection factor, i.e., a high transmittance. Parts between the central portion and the side portions

have a transmittance which is gradually increased toward the side portion. The thus manufactured mask 21 was held at a position away from the processed substrate 3 by 20 μm , and the mask 21 was illuminated with an XeCl excimer laser beam (wavelength 308 nm) from a substantially vertical direction as indicated by an arrow (FIG. 8E). As a result, a desired light intensity distribution with an inverse peak pattern (concave pattern) was formed, thereby generating a crystal with a large particle size.

A structure and an effect of a basic unit part of a mask according to a modification will now be described with reference to FIG. 9. A basic unit part 31a of a mask 31 according to a third modification is constituted by a transparent substrate 31b, and a light refraction layer 31c which is attached to an outgoing radiation plane of the substrate 31b and has light refraction characteristics according to a desired light intensity distribution with an inverse peak pattern. The light refraction layer 31c can be constituted by, e.g., forming a surface of the transparent layer into a desired curved shape or forming a desired refractive index distribution in the transparent layer.

In order to manufacture the mask 31 according to the third modification, a resist is applied on a surface of, e.g., a quartz glass substrate as the transparent layer, and an electron beam lithography and

development processing are applied while continuously or discontinuously changing a dose amount, thereby generating a resist film having a continuously or discontinuously curved surface. Thereafter, the mask
5 31 having a refraction plane with a continuously curved or stepwise surface can be obtained by using a dry etching technique. For example, by repeating formation and patterning of the resist film for a plurality of number of times, the mask 31 having a refraction plane
10 with a step-like shape can be obtained. Since the above technique has been described when forming the mask shown in FIG. 2, the detailed explanation will be eliminated.

FIG. 10 is a view showing a simulation result
15 concerning a light intensity distribution which can be obtained when using a mask that a refraction plane according to the third modification is formed into a step-like shape (formed by the latter manufacturing method). In this simulation, the refraction plane of
20 the mask 31 according to the third modification is approximated by eight level steps that a phase difference corresponds to 22.5 degrees to 180 degrees. Moreover, a numerical aperture of the illumination system 2 is set to 0.025, and a light intensity
25 distribution on the processed substrate 3 arranged away from the mask 31 by 40 μm is obtained by a calculation. As shown in FIG. 10, even if the refraction surface of

the mask 31 is approximated on multiple stages, it can be considered that a desired light intensity distribution with an inverse peak pattern (concave pattern) can be obtained as a whole.

5 A structure and an effect of a basic unit part of a mask according to a fourth modification will now be described with reference to FIG. 11. A basic unit part 41a of a mask 41 according to the fourth modification is constituted by a transparent substrate 41b, and
10 a light diffraction layer 41c which is attached or integrally formed to at least one plane of this substrate, which is a light outgoing radiation plane in this example, and has light diffraction characteristics according to a desired light intensity distribution
15 with an inverse peak pattern. The light diffraction layer 41c can be constituted by, e.g., forming at least one plane of the transparent layer into a necessary shape, or forming a predetermined refractive index distribution or a light absorption factor distribution
20 in the transparent layer. In order to realize a mask with a high diffraction efficiency (light utilization efficiency), a technique which forms the surface into a necessary shape or a technique which forms
25 a refractive index distribution inside is more preferable than a technique which forms the light absorption factor distribution inside.

 The light diffraction layer 41c is realized as

a so-called diffraction grating (or a hologram).

In the mask 41 according to the fourth modification, the light is diffracted by the diffraction grating (or the hologram), and a necessary light intensity

5 distribution is formed on the surface 3a of the processed substrate away by a predetermined distance.

In this case, as the diffraction grating (or the hologram), one having one type of interference fringe provided thereto or one having a plurality of

10 interference fringes superimposed thereon may be adopted. Additionally, the diffraction grating is classified into a non-scattering type that there is no scattering on a mask surface and a scattering type that there is scattering on a mask surface depending on
15 presence/absence of a scattering function on the mask surface. A brief description will now be given as to the non-scattering type that there is not scattering on the mask surface, i.e., a case that one type of interference fringe is provided.

20 FIG. 12 is a view schematically illustrating a basic diffraction effect of the mask according to the fourth modification. The light, which has entered with an incident angle θ the diffraction grating (or the hologram) with a cycle d formed on the mask
25 surface, undergoes the diffraction effect and is caused to outgo with an outgoing radiation angle ϕ . Here, a relationship between the incident angle θ and

the outgoing radiation angle ϕ can be represented by the following expression (3) of the diffraction.

$$\sin\theta + \sin\phi = m\lambda/d \quad (3)$$

5 In the expression (3), m is a diffraction order, and λ is a wavelength of the light. In the fourth modification, it is good enough to obtain a pitch d and a direction of the diffraction grating on the mask surface by making reference to the expression (3) in such a manner that a desired light intensity
10 distribution can be obtained on the surface 3a of the processed substrate 3 separated by a predetermined distance.

An example of a manufacturing method of the mask according to the fourth modification and a usage
15 embodiment will now be described with reference to FIG. 13. In the mask 41 according to the fourth modification, a braze type diffraction grating such as shown in FIG. 13 was formed as the light diffraction layer 41c on one surface of the transparent substrate
20 41b by the same method as that of the second modification (however, the quartz glass substrate was etched in place of the multilayer reflection film). This type of diffraction grating is called a hologram optical element or a diffraction optical element and
25 has come into practical use. This diffraction grating has a pitch which varies in a one-dimensional direction, and has a function to linearly condense

the light onto its focal position. The manufactured non-scattering type (one type of interference fringe) mask 41 was held at a position away from the processed substrate 3 by a focal distance D so as to face this substrate then, the mask 41 was illuminated with an XeCl excimer laser beam (wavelength: 308 nm) in a non-parallel light beam (scattered light flux) having a predetermined maximum incident angle from a substantially vertical direction.

As a result, a desired light intensity distribution with an inverse peak pattern (concave pattern) was formed, thereby generating a crystal with a large particle size. Such a diffraction type mask can be manufactured by hologram type exposure. In this case, it is good enough to generate a linear object light beam by using optical means such as a slit or a cylindrical lens, and record an interference fringe of the linear object light and a reference light beam onto a hologram sensitive material. Even if the hologram type recording method is used or the manufacturing method based on the above calculation is used, both the scattering type and non-scattering type conformations can be realized.

It is to be noted that the basic unit part of the mask forms the one-dimensional light intensity distribution and the mask has a conformation that the basic unit part is one-dimensionally repeated along

a direction of the light intensity distribution in the above-described embodiment and modifications.

However, the present invention is not restricted thereto, the basic unit part of the mask can form

5 a two-dimensional light intensity distribution and the mask can have a conformation that the basic unit part is two-dimensionally repeated along a direction of the light intensity distribution.

A structure of a crystallization apparatus
10 according to a second embodiment of the present invention will now be described with reference to FIG. 14. Although the second embodiment has a structure similar to that of the first embodiment, the second embodiment is basically different from the
15 first embodiment in that the light outgoing radiation plane of the mask 1 and the light incident plane of the processed substrate 3 are arranged in contact with each other. As described above, in the first embodiment according to a so-called defocus method, it
20 is possible to use the light absorption type mask 1, the light scattering type mask 11, the light reflection type mask 21, the light refraction type mask 31 and the light diffraction type mask 41.

On the contrary, in the second embodiment
25 according to a contact method, it is possible to employ the light absorption type mask 1, the light scattering type mask 11 and the light reflection type mask 21, but

the light refraction type mask 31 and the light diffraction type mask 41 cannot be used. Further, as described above, when the forward scattered light reaches the processed substrate and forms the noise,
5 the light scattering type mask 11 can be used in the second embodiment.

A structure of a crystallization apparatus according to a third embodiment of the present invention will now be described with reference to
10 FIG. 15. Although the third embodiment has a structure similar to that of the first embodiment, the third embodiment is basically different from the first embodiment in that an image forming optical system 5 is provided in a light path between the mask 1 and the
15 processed substrate 3. In the third embodiment, as shown in FIG. 15, the processed substrate 3 is set away from a surface (image plane of the image forming optical system 5) optically conjugate with the mask 1 by a predetermined distance on an optical axis. This
20 image forming optical system 5 may be a refraction type optical system, a reflection type optical system or a refraction/reflection optical system. In the third embodiment according to a so-called projection defocus method, it is possible to use the light absorption type
25 mask 1, the light scattering type mask 11, the light reflection type mask 21, the light refraction type mask 31 and the light diffraction type mask 41 like

the first embodiment.

In the first and second embodiment, it is necessary to give attention to abrasion in the processed substrate. On the contrary, in the third
5 embodiment, the image forming optical system 5 is interposed between the mask 1 and the processed substrate 3. Thus, a relatively large gap is assured between the processed substrate 3 and the image forming optical system 5. Accordingly, the excellent
10 crystallization can be realized without being affected by abrasion in the processed substrate.

In the third embodiment, since a relatively large gap may be assured between the processed substrate 3 and the image forming optical system 5, it is easy to
15 lead a detection light beam used to detect a position into a light path between these members and adjust a positional relationship between the processed substrate 4 and the image forming optical system 5.

FIG. 16 schematically shows a structure of
20 a crystallization apparatus according to a fourth embodiment of the invention. Although the fourth embodiment has a structure similar to that of the third embodiment, the fourth embodiment is basically different from the third embodiment in that the mask 1
25 and the processed substrate 3 are arranged so as to be optically conjugate through the image forming optical system 6. Paying attention to the difference from the

third embodiment, the fourth embodiment will now be described.

In the fourth embodiment, the image forming optical system 6 has an aperture diaphragm 6a arranged on its pupil plane. The aperture diaphragm 6a is selected as one of a plurality of aperture diaphragms having different aperture portions (light transmission portions), and a plurality of the aperture diaphragms are constituted so as to be capable of being switched with respect to the light path. Alternatively, the aperture diaphragm 6a has one iris diaphragm which can continuously change a size of an aperture portion. In both cases, a size of the aperture of the aperture diaphragm 6a (namely, an image side numerical aperture of the image forming optical system 6) is set so as to generate a necessary light intensity distribution with an inverse peak pattern on a semiconductor film of the processed substrate 3.

In the fourth embodiment according to a so-called projection NA method, it is possible to use the light absorption type mask 1, the light scattering type mask 11, the light reflection type mask 21, the light refraction type mask 31 and the light diffraction type mask 41 like the first and third embodiments. Furthermore, in the fourth embodiment, the excellent crystallization can be realized without being affected by abrasion in the processed substrate 3, and

a positional relationship between the processed substrate 3 and the image forming optical system 6 can be adjusted like the third embodiment.

5 A crystallization apparatus according to a fifth embodiment of the present invention will now be described with reference to FIG. 17. Although the fifth embodiment has a structure similar to that of the first embodiment, the fifth embodiment is basically different from the first embodiment in that the mask 51
10 has two function layers. As shown in FIG. 17, the basic unit part 51a of the mask 51 includes a light refraction layer 51b having light refraction characteristics according to a desired light intensity distribution with an inverse peak pattern, and a light
15 absorption layer 51c having light absorption characteristics according to a desired light intensity distribution with an inverse peak pattern.

Here, the light refraction layer 51b arranged with a predetermined gap from the surface 3a of the
20 processed substrate forms on the surface 3a a light intensity distribution with a gentle inverse peak pattern (concave pattern) like a curved line indicated by a broken line 51bb in the figure. On the other hand, the light absorption layer 51c arranged in close
25 proximity to (or appressed against) the surface 3a of the processed substrate forms on the surface 3a a light intensity distribution with an inverse peak which is

steeper than that obtained by the light refraction layer 51b,

As a result, in the fifth embodiment using the mask 51, a light intensity distribution with
5 a two-stage inverse peak pattern can be obtained on the surface 3a of the processed substrate like a curved line indicated by a solid line 51bc in FIG. 17 by a combination of the effect of the light refraction layer 51b and the effect of the light absorption
10 layer 51c. In the light intensity distribution with the two-stage inverse peak pattern shown in FIG. 17, after the light intensity is suddenly increased from a position where the light intensity is 0 or minimum toward the laterally and reaches a predetermined value,
15 the light intensity is further substantially monotonously increased in a lateral direction. At the position where the light intensity is substantially 0 or minimum, although not a must, it is desirable to set the light intensity in such a manner that a temperature
20 of the surface 3a becomes not more than a fusing point of a substance forming this surface, e.g., amorphous silicon. In the fifth embodiment, a crystal nucleus or nuclei are formed in the vicinity of a position or positions where the light intensity is minimum in the
25 light intensity distribution with the two-stage inverse peak pattern. Subsequently, a lateral growth starts from the crystal nucleus toward the periphery along

a direction that a light intensity gradient (in other words, a temperature gradient) is large. At this time, in the light intensity distribution with the two-stage inverse peak pattern which can be obtained by the mask according to the present invention, a part where the light intensity is decreased does not substantially exist in the middle portion, as different from the prior art. Thus, a growth of a large crystal grain can be realized without stopping the lateral growth in mid course.

When trying to obtain such a light intensity distribution with the two-stage inverse peak pattern by only the light absorption layer 51c, a change in film thickness of the light absorption layer 51c becomes large. However, there is an advantage that a film thickness distribution of the light absorption layer 51c is no longer necessary or very small, since a combination of the two function layers is utilized in the fifth embodiment. Likewise, when trying to obtain the light intensity distribution with the two-stage inverse peak pattern by only the light refraction layer 51b, a surface shape or a refractive index distribution of the light refraction layer 51b becomes very complicated. However, forming the light intensity distribution with the concave pattern by the light refraction layer 51b can suffice since the combination of the two function layers is utilized, and

a relatively simple surface shape or refractive index distribution is enough.

5 In the fifth embodiment, although the mask 51 having the light refraction layer 51b and the light absorption layer 51c is used, the present invention is not restricted to this combination of the function layers. It is possible to use a mask having two or more any different function layers or two or more any equal function layers. Specifically, as the first and
10 second function layers constituting the mask, arbitrary function layers can be selected from the light absorption layer, the light scattering layer, the light reflection layer, the light refraction layer and the light diffraction layer.

15 Although the light refraction layer 51b and the light absorption layer 51c are arranged with a gap therebetween in the fifth embodiment, the present invention is not restricted thereto. The two function layers may be formed or arranged integrally or without
20 a gap therebetween. As to the arrangement of the two function layers, various modifications can be carried out. Specifically, when giving, e.g., a refraction surface to a light absorption material, the light absorption layer and the light refraction layer are
25 integrally formed. Further, when giving, e.g., a phase shift plane to the light absorption material, the light absorption layer and the phase shift layer are

integrally formed. FIG. 17A shows this example.

This mask 100 is formed by using a phase shifter 100a such as shown in FIG. 22 as a transparent substrate and attaching a light absorption layer 100c such as shown

5 in FIG. 2 as a function layer to the light outgoing radiation plane. Here, the function layer is not restricted to the light absorption layer, and it can be understood by a person skilled in the art that the function layer can be selected from the light
10 absorption layer having light absorption characteristics according to a light intensity distribution with an inverse peak pattern, the scattering layer, the light reflection layer, the light refraction layer and the light diffraction layer.
15 Furthermore, it can be understood that any of the function layer and the phase shifter may be arranged on the light incident side.

Although the present invention is applied to the crystallization apparatus and method according to the
20 defocus method in the fifth embodiment, the present invention is not restricted thereto. The present invention can be also applied to the crystallization apparatus and method according to a contact method, a projection defocus method or a projection NA method.

25 An example of a manufacturing method of a mask in which a light reflection layer and a light absorption layer are integrally constituted and a usage embodiment

will now be described with reference to FIGS. 18A to 18C. In this manufacture embodiment, a light reflection layer 53 consisting of a multilayer reflection film having a predetermined layer number distribution was formed on, e.g., a quartz glass substrate 52 as shown in FIG. 18A by the method described in connection with the second modification of the first embodiment. Subsequently, a chrome layer was formed on a thickest area of the light reflection layer 53 by sputtering, and resist application, exposure, development and etching were carried out, thereby forming a light absorption layer 54 consisting of a chrome pattern as shown in FIG. 18B.

The manufactured mask 55 was held at a position in contact with the processed substrate 3 or held at a position away from the processed substrate 3 by a predetermined distance as shown in FIG. 18C. Then, the mask 55 was illuminated with an XeCl excimer laser beam (wavelength: 308 nm) as indicated by an arrow from a substantially vertical direction. As a result, a desired light intensity distribution with a two-stage inverse peak pattern was formed, and a crystal with a large particle size was generated. Here, the light reflection layer 53 has a function to form a light intensity distribution with a gentle inverse peak pattern (concave pattern). The light absorption layer 54 has a function to form a light intensity

distribution with a steep inverse peak pattern.

A mask used in a crystallization apparatus according to a sixth embodiment of the present invention and its effect will now be described with reference to FIGS. 19A to 19DC. The sixth embodiment has a structure similar to that of the first embodiment, but the sixth embodiment is basically different from the first embodiment in that a mask 61 has binary distribution characteristics. In a basic unit part 61a of the mask 61 according to the sixth embodiment, many small light absorption unit areas 61c are discretely formed on, e.g., a quartz glass substrate 61b according to a predetermined dot distribution. In this example, the light absorption unit area 61c has a circular shape, and a gap between the areas becomes wider toward the outer side in the lateral direction (horizontal direction in FIG. 19D) and even in the lengthwise direction.

The shape and the distribution of the light absorption unit area 61c are not restricted to the above structure. They can be arbitrarily set in accordance with a necessary light intensity pattern. For example, as shown in FIG. 19E, the light absorption unit area 61c may have an elongated layer shape.

As shown in FIG. 19B, a strip-like discontinuous light intensity distribution can be obtained on the outgoing radiation plane of the mask 61 having

the above structure. However, a light intensity distribution with a relatively continuous inverse peak pattern can be obtained on the surface 3a of the processed substrate away from the outgoing radiation plane of the mask 61 with a gap therebetween by removing a high-frequency component of a spatial frequency by utilizing the defocus as show in FIG. 19C.

Although the small light absorption unit areas 61c formed in accordance with a predetermined distribution are used in the sixth embodiment, the present invention is not restricted thereto. It is also possible to use, e.g., small light scattering unit areas or light reflection unit areas formed in accordance with a predetermined distribution (however, small light refraction unit areas or small light diffraction unit areas cannot be used). That is, in general, a continuous light intensity distribution can be obtained by using a mask having a binary structure in place with distribution characteristics continuous in terms of a material or a structure, and cutting (removing) a high-frequency component of a spatial frequency. In this case, difficult processing to realize a distribution continuous in terms of a material or a structure is no longer necessary.

Although the high-frequency component is removed by separating the outgoing radiation plane of the mask 61 from the surface 3a of the processed substrate in

the sixth embodiment, the present invention is not restricted thereto. The high-frequency component can be removed by separating the processed substrate from a surface which is optically conjugate with the mask through the image forming optical system arranged in the light path between the processed substrate and the mask, for example. Specifically, for example, in the apparatus shown in FIG. 15, using the mask 61 according to this embodiment as the mask 1 can suffice.

Moreover, in the defocus method or the projection defocus method in particular, the high-frequency component can be also removed by illuminating the mask with a non-parallel light flux having a predetermined maximum incident angle.

Additionally, the high-frequency component can be also removed by arranging the processed substrate and the mask so as to be optically substantially conjugate with each other through the image forming optical system, and setting an image side numerical aperture of the image forming optical system to a necessary value. Further, by giving a necessary aberration to the image forming optical system arranged in the light path between the processed substrate and the mask.

A brief description will now be given as to a case that the high-frequency component is removed by setting the image side numeral aperture of the image forming optical system to a necessary value. A complex

amplitude distribution $I(u, v)$ of an image through the image forming optical system can be represented by a convolution integral of a complex amplitude distribution $O(u, v)$ of an object (mask) and a complex amplitude distribution of a point image (point spread function) $ASF(u, v)$ as indicated by the following expression (4). It is to be noted that " \int " is an integral symbol in the expression (4).

$$I(u, v) = \iint |O(u', v') ASF(u-u', v-v')| du' dv' \quad (4)$$

Here, the point spread function ASF is given by Fourier transform of a pupil function. That is, when the image side numeral aperture of the image forming optical system is small, the point spread function has a wider distribution, and blurring of an image becomes large. This means that a high-frequency component in a spatial frequency of the object is cut, and serves as one type of high-cut filter. As a result, even if the object is a binary type, the high-frequency component is cut, thereby obtaining a continuous light intensity distribution.

An example of a manufacturing method of a mask having binary distribution characteristics and a usage embodiment will now be described with reference to FIG. 20. In this manufacture embodiment, a chrome mask is used as a mask. That is, as shown in FIG. 20, a basic unit part 61a of a mask 61 was manufactured by

forming a small chrome area 61c on a transparent substrate 61b so as to be distributed in the binary manner based on a pattern such that a numeral aperture is entirely increased as distanced from the center.

5 In case of the chrome mask, the chrome layer 61c functions as a light absorption layer and also as a light reflection layer.

A high-frequency component was cut by applying the thus manufactured mask to the projection NA method and
10 setting the image side numerical aperture of the image forming optical system to 0.05. As a result, a desired light intensity distribution with an inverse peak pattern (concave pattern) or a two-stage peak pattern was formed, thereby generating a crystal with a large
15 particle size. It is to be noted that only the numeral aperture in one direction is modulated in the example of FIG. 20, but only the numerical aperture in the other direction may be modulated, or the numerical aperture may be two-dimensionally modulated along the
20 both directions. Moreover, a density of a small aperture having a fixed size can be modulated.

In each of the foregoing embodiments, although the light intensity distribution can be calculated on a design stage, it is desirable to observe and confirm
25 the light intensity distribution on the actual processed plane (exposed plane). Therefore, it is good enough to enlarge the processed plane by the optical

system and input a result by an imaging element such as a CCD. When the light to be used is ultraviolet rays, since the optical system undergoes restriction, the light may be converted into visible light rays by providing a fluorescent screen to the processed plane.

An example of a method for manufacturing an electronic device by using the crystallization apparatus according to each embodiment will now be described with reference to FIGS. 21A to 21E. As shown in FIG. 21A, an underlying film 81 (e.g., SiN having a film thickness of 50 nm and an SiO₂ laminated film having a film thickness of 100 nm) and an amorphous semiconductor film 82 (e.g., Si, Ge, SiGe or the like having a film thickness of approximately 50 nm to 200 nm) are sequentially formed on, e.g., a rectangular insulating substrate 80 (e.g., alkali glass, quartz glass, plastic, polyimide or the like) having flat both surfaces by using a chemical vapor deposition method or a sputtering method, thereby forming the processed substrate 3. Then, a part of the upper surface or all of the upper surface of the amorphous semiconductor film 82 (corresponding to the surface 3a of the processed substrate 3) is irradiated with a laser beam 83 (e.g., a KrF excimer laser beam or an XeCl excimer laser beam) as indicated by arrows by using the crystallization apparatus according to each embodiment.

As a result, as shown in FIG. 21B, the amorphous

semiconductor film 82 becomes a polycrystal
semiconductor film or a monocrystal semiconductor film
84 having a crystal grain or grains with a large
particle size. Then, as shown in FIG. 21C, the
5 polycrystal semiconductor film or the monocrystal
semiconductor film is processed into an island-shaped
semiconductor film 85 by using the photolithography
technique. Then, an SiO_2 film having a film thickness
of 20 nm to 100 nm is formed as a gate insulating film
10 86 on the semiconductor film 85 and the underlying
layer 81 by using the chemical vapor deposition method
or the sputtering method. Additionally, as shown in
FIG. 21D, a gate electrode 87 (e.g., silicide or MoW)
is formed on a part opposed to the semiconductor film
15 85, of the gate insulating film 86. Then, impurity
ions 88 (phosphor in case of an N channel transistor,
boron in case of a P channel transistor) are implanted
into the semiconductor layer 85 through the gate
insulating film 86 as indicated by arrows with the gate
20 electrode 87 being used as a mask. Thereafter,
annealing processing (e.g., one hour at 450°C) is
carried out in a nitrogen atmosphere, the impurities in
the semiconductor layer 85 are activated. Thus,
a source area 91 and a drain area 92 are formed with
25 a channel area 90 positioned below the gate electrode
87 being sandwiched therebetween.

Subsequently, as shown in FIG. 21E, an interlayer

insulating film 89 is formed on the gate insulating film 86 and the gate electrode 87. Next, contact holes are formed to these films 86 and 89, and a source electrode 93 and a drain electrode 94 connected to the source area 91 and the drain area 92 are formed. At this time, the channel area 90 is formed in accordance with a position of the crystal with a large particle size of the polycrystal semiconductor film or the monocrystal semiconductor film 84 formed by emitting the laser beam through the mask described in each modification, in the steps shown in FIGS. 21A and 21B. With the above-described steps, a polycrystal transistor or a monocrystal semiconductor transistor can be formed. The manufactured polycrystal transistor or monocrystal transistor can be applied to a drive circuit of, e.g., a liquid crystal display or an EL (electro luminescence) display or an integrated circuit such as a memory (SRAM or DRAM) or a CPU.

Although the present invention is applied to the crystallization apparatus and method in each of the foregoing embodiments, the present invention is not restricted thereto, and the present invention can be generally applied to a mask used to form a predetermined light intensity distribution on a predetermined plane and an exposure method used to form a predetermined light intensity distribution on a substrate set on a predetermined plane by using

this mask.

Additional advantages and modifications will readily occur to those skilled in the art. Therefore, the invention in its broader aspects is not limited to the specific details and representative embodiments shown and described herein. Accordingly, various modifications may be made without departing from the spirit or scope of the general invention concept as defined by the appended claims and their equivalents.